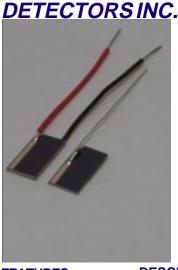
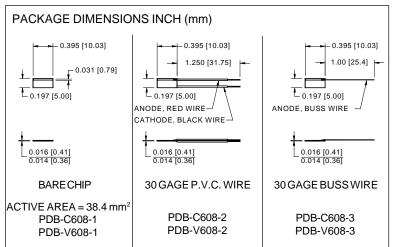
PHOTONIC Silicon Photodiode, Blue Enhanced Solderable Chips

Photoconductive Type PDB-C608 Photovoltaic Type PDB-V608





FEATURES

- Blue enhanced
- Photovoltaic type
- Photoconductive type
- High quantum efficiency

DESCRIPTION: Low cost blue enhanced planar diffused silicon solderable photodiode. The PDB-V608 cell is designed

for low noise, photovoltaic applications. The PDB-C608 cell is designed for low capacitance, high speed, photoconductive

operation. They are available bare, PVC or buss wire leads.

APPLICATIONS

- Optical encoder
- Position sensor
- Industrial controls
- Instrumentation

ABSOLUTE MAXIMUM RATING (TA=25°C unless otherwise noted)

SYMBOL	PARAMETER .	PDB-	C608	PDB-	V608	UNITS
01111202	17000021210		MAX	MIN	MAX	00
VBR	Reverse Voltage		75		25	V
T _{STG}	Storage Temperature	-40	+125	-40	+125	°C
То	Operating Temperature Range	-40	+100	-40	+100	∘C
Ts	Soldering Temperature		+224		+224	°C
I	Light Current		500		500	mA

SPECTRAL RESPONSE 0.7 RESPONSIVITY (A/W) 0.6 0.5 0.4 0.3 0.2

009 200 400 500 800 WAVELENGTH (nm)

0.1

ELECTRO-OPTICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

SYMBOL	CHARACTERISTIC	TESTCONDITIONS	PDB-C608			PDB-V608			LINITO
			MIN	TYP	MAX	MIN	TYP	MAX	UNITS
Isc	Short Circuit Current	H = 100 fc, 2850 K	455	475		455	475		μ A
ΙD	Dark Current	H = 0, V _R = 5 V*		25	50		40	80	nA
Rsh	Shunt Resistance	H = 0, V _R = 10 mV	5	10		8	20		MΩ
TC Rsh	RsH Temp. Coefficient	H = 0, V _R = 10 mV		-8			-8		%/°C
Сл	Junction Capacitance	H = 0, V _R = 5 V**		200			5000		pF
λrange	Spectral Application Range	Spot Scan	350		1100	350		1100	nm
λр	Spectral Response - Peak	Spot Scan		940			940		nm
V _{BR}	Breakdown Voltage	I = 10 μA	25	50		5	15		V
NEP	Noise Equivalent Power	V _R = 0 V @ Peak	2.5 x 10 ⁻¹³ TYP		1 x 10 ⁻¹³ TYP			W/ √Hz	
tr	Response Time	$RL = 1 K\Omega V_R = 5 V^{**}$		28			1200		nS

^{*}VR = 100 mV on Photovoltaic type **VR = 0 V on Photovoltaic type